

2MBI150VH-170-50

IGBT Modules

IGBT MODULE (V series) 1700V / 150A / 2 in one package

■ Features

- High speed switching
- Voltage drive
- Low Inductance module structure

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial machines, such as Welding machines

■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units	
Collector-Emitter voltage	V _{CEs}		1700	V	
Gate-Emitter voltage	V _{GES}		±20	V	
Collector current	I _c	Continuous	T _c =25°C	150	A
			T _c =100°C	250	
	I _{c pulse}	1ms	300		
	-I _c		150		
	-I _{c pulse}	1ms	300		
Collector power dissipation	P _C	1 device	1110	W	
Junction temperature	T _j		175		
Operating junction temperature (under switching conditions)	T _{jop}		150	°C	
Case temperature	T _c		125		
Storage temperature	T _{stg}		-40 ~ 125		
Isolation voltage	V _{iso}	AC : 1min.	4000	VAC	
Screw torque	Mounting (*2)		6.0	N m	
	Terminals (*3)		5.0		

Note *1: All terminals should be connected together during the test.

Note *2: Recommendable Value : 3.0-6.0 N·m (M5 or M6)

Note *3: Recommendable Value : 2.5-5.0 N·m (M5)

● Electrical characteristics (at T_j = 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero gate voltage collector current	I _{CEs}	V _{GE} = 0V, V _{CE} = 1700V	-	-	2.0	mA	
Gate-Emitter leakage current	I _{GES}	V _{CE} = 0V, V _{GE} = ±20V	-	-	400	nA	
Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} = 20V, I _c = 150mA	6.0	6.5	7.0	V	
Collector-Emitter saturation voltage	V _{CE(sat)} (terminal)	V _{GE} = 15V I _c = 150A	T _j =25°C	-	2.20	2.65	V
			T _j =125°C	-	2.60	-	
			T _j =150°C	-	2.65	-	
	V _{CE(sat)} (chip)		T _j =25°C	-	2.00	2.45	
			T _j =125°C	-	2.40	-	
			T _j =150°C	-	2.45	-	
Internal gate resistance	R _{G(int)}	-	-	5.0	-	Ω	
Input capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz	-	16	-	nF	
Turn-on time	t _{on}	V _{CC} = 900V, I _c = 150A V _{GE} = ±15V, R _{g_on} =R _{g_off} = 4.8Ω	-	950	-	nsec	
	t _r		-	350	-		
	t _(l)		-	60	-		
Turn-off time	t _{off}	T _j =150°C, L _s = 30nH	-	1050	-	nsec	
	t _r		-	140	-		
			-	-	-		
Forward on voltage	V _F (terminal)	V _{GE} = 0V I _F = 150A	T _j =25°C	-	1.95	2.40	V
			T _j =125°C	-	2.20	-	
			T _j =150°C	-	2.20	-	
	V _F (chip)		T _j =25°C	-	1.80	1.95	
			T _j =125°C	-	2.05	-	
			T _j =150°C	-	2.05	-	
Reverse recovery time	t _{rr}	I _F = 150A	-	220	-	nsec	

● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance(1device)	R _{th(j-c)}	IGBT	-	-	0.135	°C/W
		FWD	-	-	0.200	
Contact thermal resistance (1device) (*4)	R _{th(c-f)}	with Thermal Compound	-	0.0250	-	

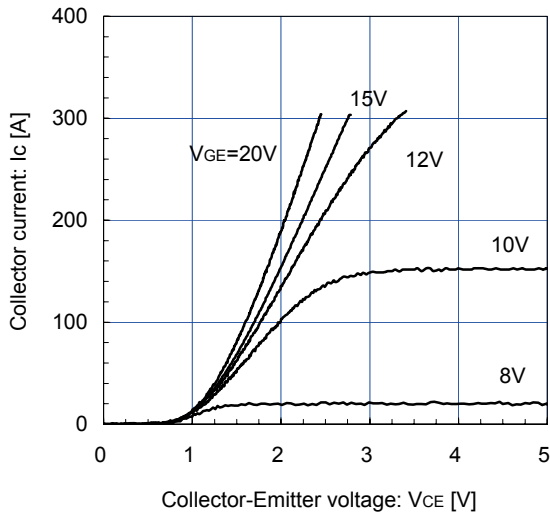
Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

Package No. : M276

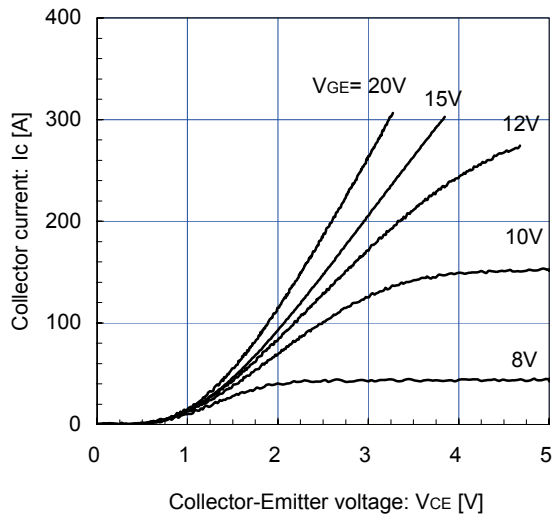


■ Characteristics (Representative)

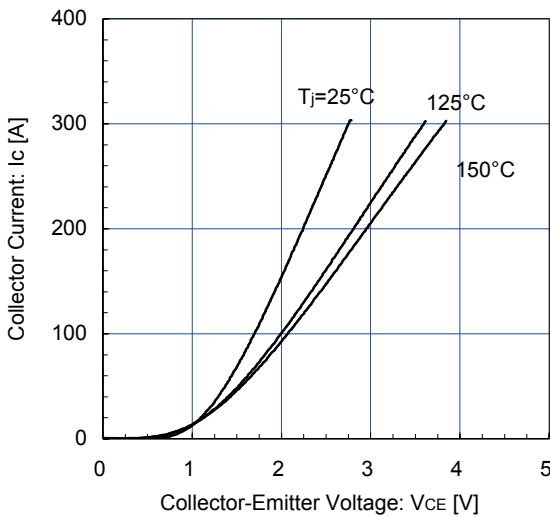
Collector current vs. Collector-Emittter voltage (typ.)
 $T_j = 25^\circ\text{C}$ / chip



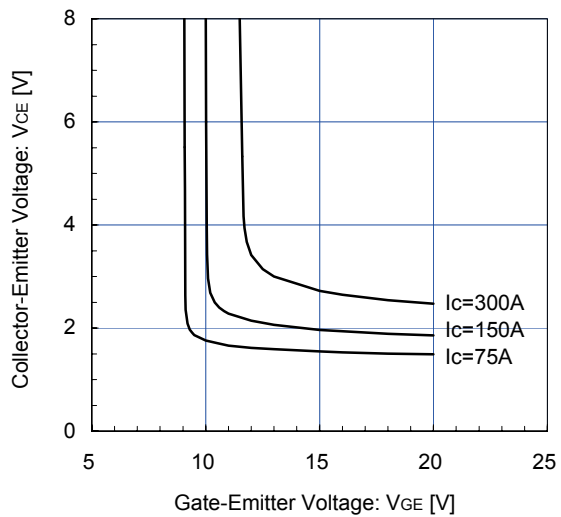
Collector current vs. Collector-Emittter voltage (typ.)
 $T_j = 150^\circ\text{C}$ / chip



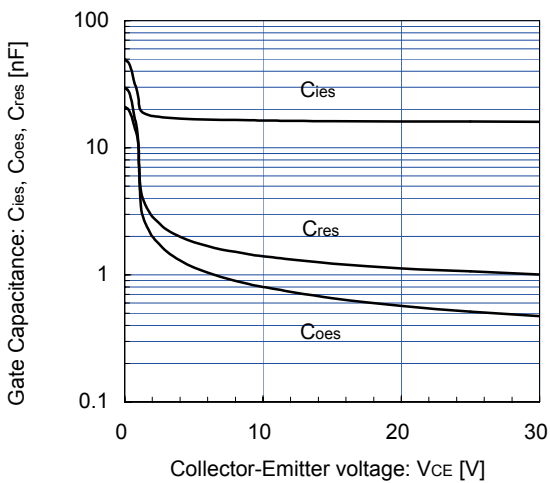
Collector current vs. Collector-Emittter voltage (typ.)
 $V_{GE} = 15\text{V}$ / chip



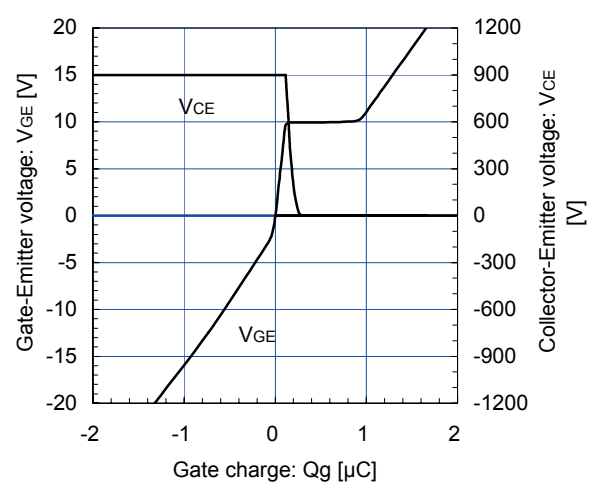
Collector-Emittter voltage vs. Gate-Emittter voltage
 $T_j = 25^\circ\text{C}$ / chip



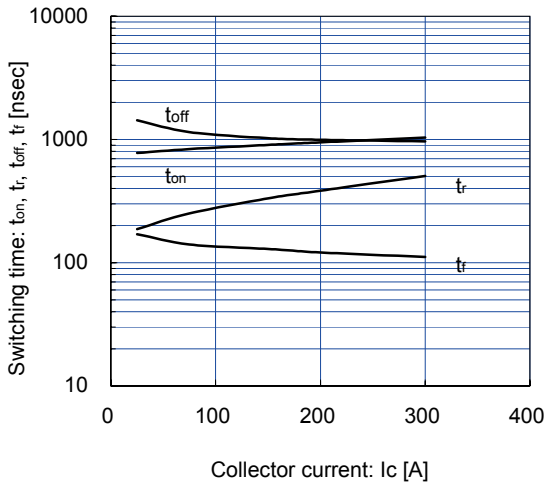
Gate Capacitance vs. Collector-Emittter Voltage
 $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $T_j = 25^\circ\text{C}$



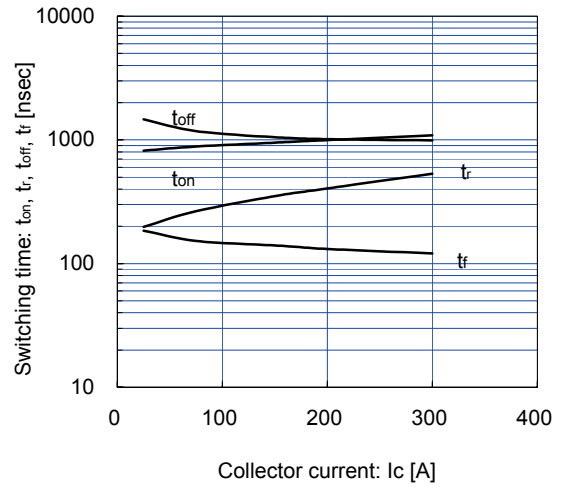
Dynamic Gate Charge (typ.)
 $V_{CC} = 900\text{V}$, $I_c = 150\text{A}$, $T_j = 25^\circ\text{C}$



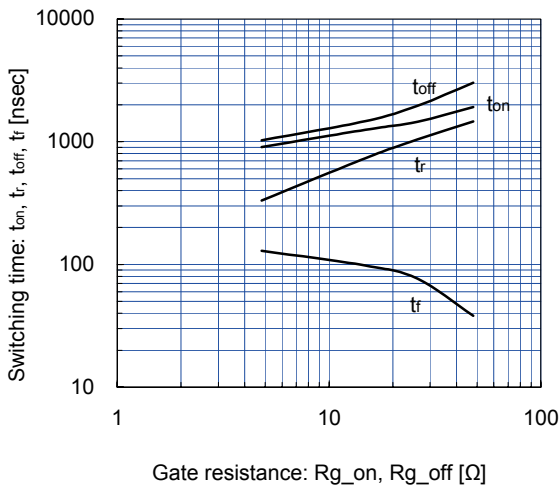
Switching time vs. Collector current (typ.)
 $V_{CC}=900V, V_{GE}=\pm 15V, R_{g_on}=R_{g_off}=4.8\Omega, T_j=125^\circ C$



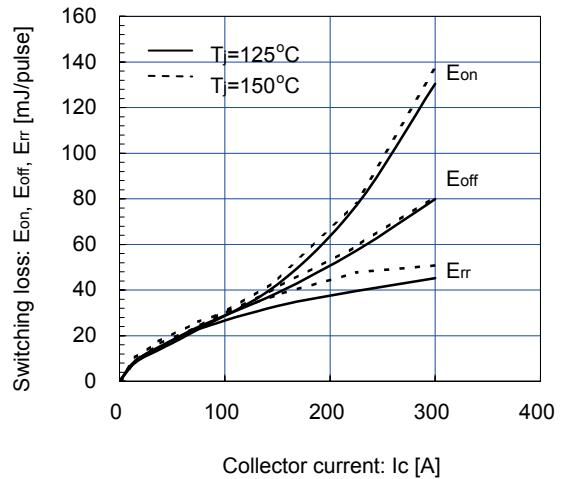
Switching time vs. Collector current (typ.)
 $V_{CC}=900V, V_{GE}=\pm 15V, R_{g_on}=R_{g_off}=4.8\Omega, T_j=150^\circ C$



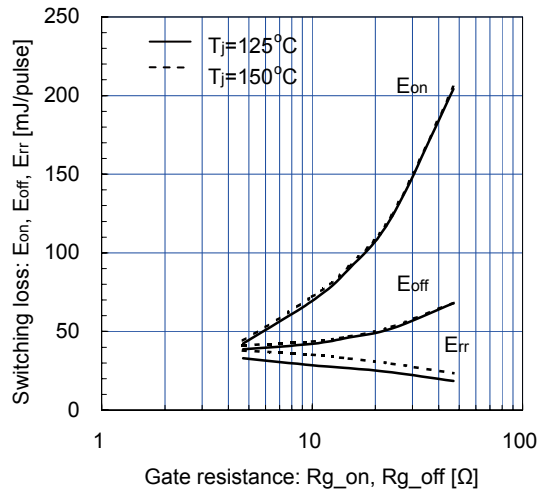
Switching time vs. Gate resistance (typ.)
 $V_{CC}=900V, I_c=150A, V_{GE}=\pm 15V, T_j=125^\circ C$



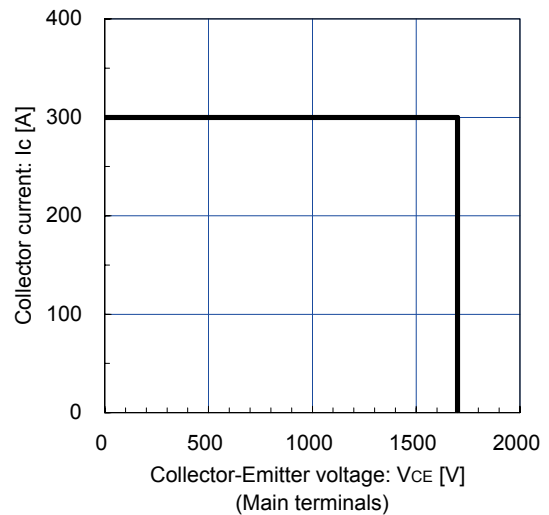
Switching loss vs. Collector current (typ.)
 $V_{CC}=900V, V_{GE}=\pm 15V, R_{g_on}=R_{g_off}=4.8\Omega, T_j=125, 150^\circ C$



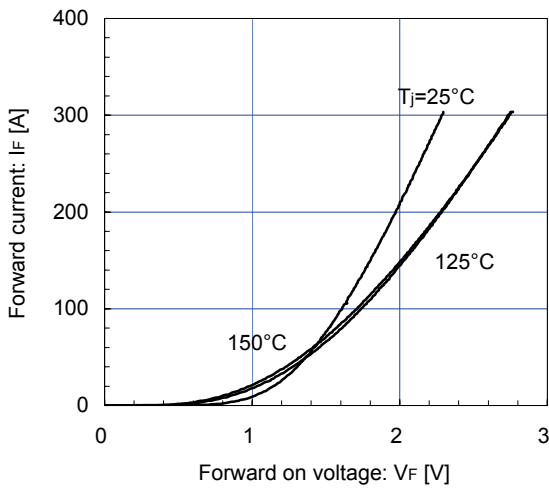
Switching loss vs. Gate resistance (typ.)
 $V_{CC}=900V, I_c=150A, V_{GE}=\pm 15V, T_j=125, 150^\circ C$



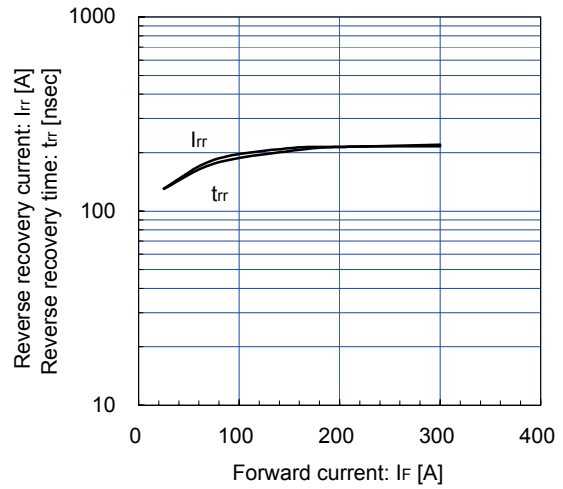
Reverse bias safe operating area (max.)
 $+V_{GE}=15V, -V_{GE}=15V, R_{g_off}=4.8\Omega, T_j=150^\circ C$



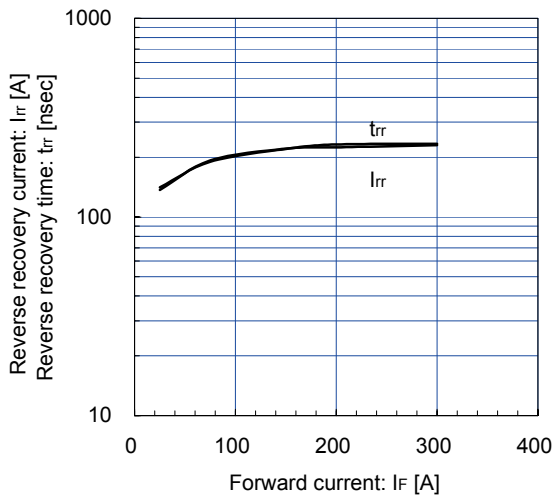
Forward Current vs. Forward Voltage (typ.)
chip



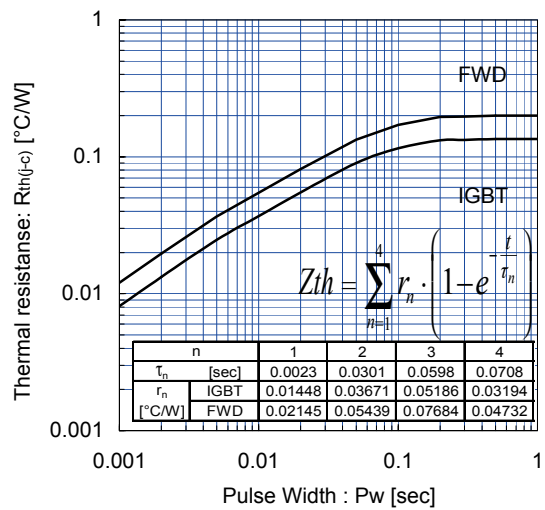
Reverse Recovery Characteristics (typ.)
VCC=900V, VGE=±15V, Rg_on=4.8Ω, Tj=125°C



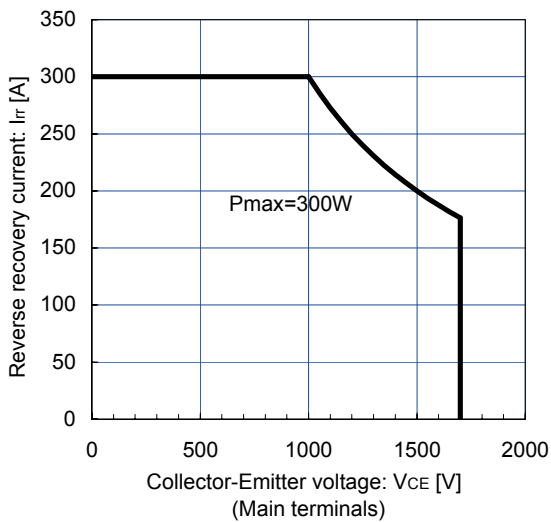
Reverse Recovery Characteristics (typ.)
VCC=900V, VGE=±15V, Rg_on=4.8Ω, Tj=150°C



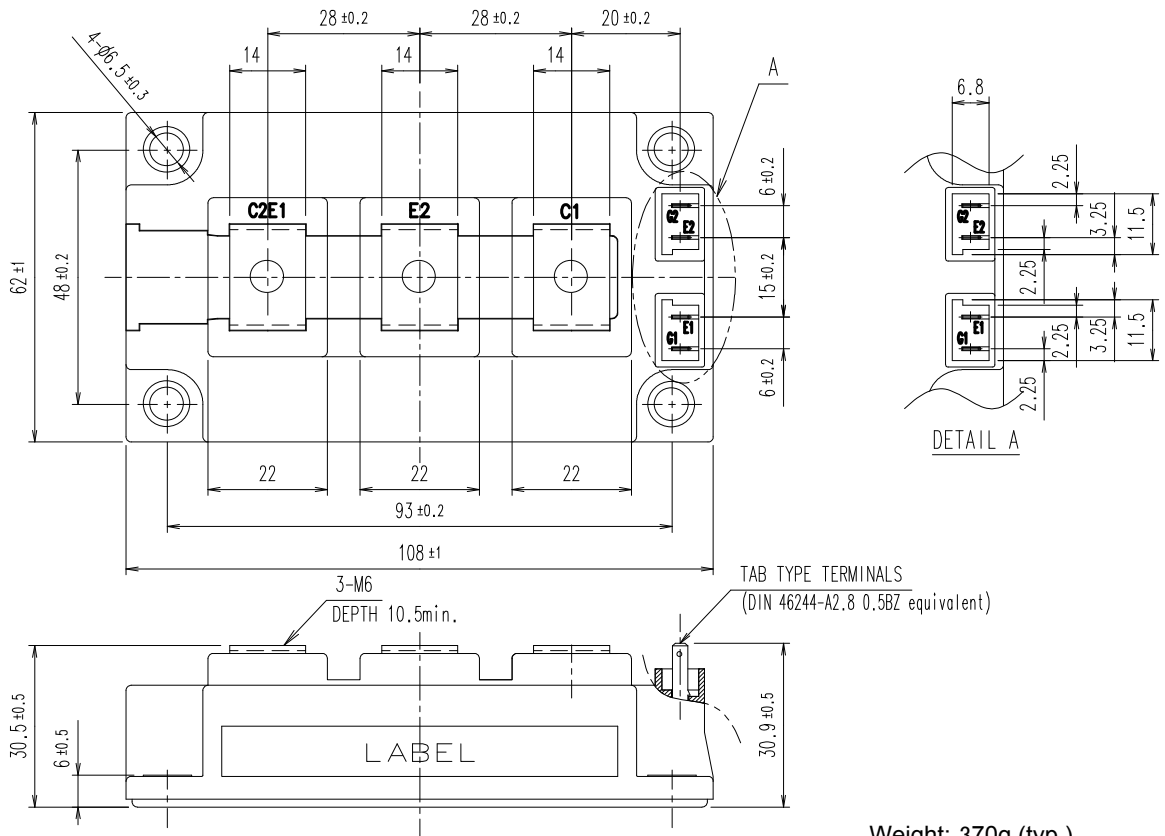
Transient Thermal Resistance (max.)



FWD safe operating area (max.)
Tj=150°C

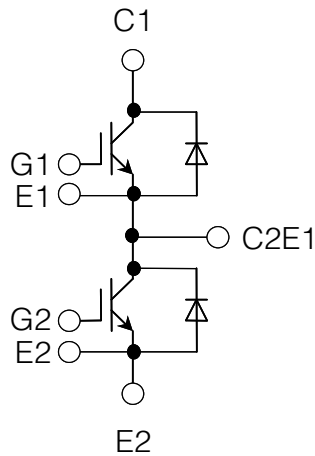


■ Outline Drawings, mm



Weight: 370g (typ.)

■ Equivalent Circuit Schematic



WARNING

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 - Machine tools
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 - Electrical home appliances
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